

EPISTAR

ES-EABCF08W

InGaN F-series LED Chip

> Mechanical Specification:

(1) Dimension

- Chip size: 8mill x 40mil ($215 \pm 25 \mu\text{m}$ x $1016 \pm 25 \mu\text{m}$)
- Thickness: 5.3mil ($135 \pm 10 \mu\text{m}$)
- P bonding pad: 2.4mil ($60 \pm 10 \mu\text{m}$)
- N bonding pad: 2.4mil ($60 \pm 10 \mu\text{m}$)

(2) Metallization

- Topside P electrode: Au alloy
- Topside N electrode: Au alloy



Features:

- High radiant flux
- 100% probing test
- Passivation layer on top
- Long operation life

Applications:

- Backlight

> Electro-optical Characteristics at 25°C:⁽¹⁾

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf1	If = 10µA	2.0	-	-	V
	Vf2	If = 20mA	-	2.8	2.9	V
Reverse Current	Ir	Vr = 5V	-	-	2.0	µA
Dominant Wavelength⁽²⁾	λd	If = 20mA	445	-	455	nm
Spectra Half-width	Δλ	If = 20mA	-	25	-	nm
Radiant Flux⁽³⁾⁽⁴⁾	Po	If = 20mA	42	-	43	mW
			43	-	44	
			44	-	45	
			45	-	46	
			46	-	47	

Note:

(1) ESD protection during chip handling is recommended.

(2) Basically, the wavelength span is 10nm; however, customers' special requirements are also welcome.

(3) Radiant flux is determined by using an Ag-plated TO-can header without an encapsulant.

(4) Radiant flux measurement allows a tolerance of ±15%.

> Absolute Maximum Ratings:

Parameter	Symbol	Condition	Rating	Unit
Forward DC Current	If	T _a = 25°C	≤ 60	mA
Reverse Voltage	V _r	T _a = 25°C	≤ 5	V
Junction Temperature	T _j	-	≤ 125	°C
Storage Temperature	T _{stg}	Chip	-40 ~ +85	°C
		Chip-on-tape/storage	5 ~ 35	°C
		Chip-on-tape/transportation	-20 ~ +65	°C
Temperature during Packaging	-	-	280(<10sec)	°C

Note: Maximum ratings are package dependent. The above maximum ratings were determined using a Printed Circuit Board (PCB) without an encapsulant. Stresses in excess of the absolute maximum ratings such as forward current and junction temperature may cause damage to the LED.

> Characteristic Curves:

Fig.1 – Relative luminous Intensity vs. Forward Current

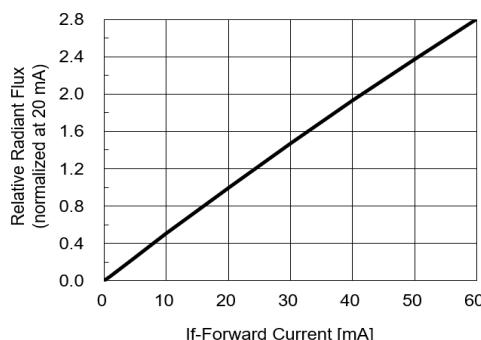


Fig.2 – Forward Current vs. Forward Voltage

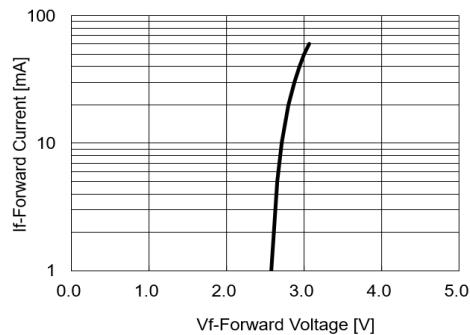


Fig.3 – Relative Intensity (@20mA) vs. Ambient Temperature

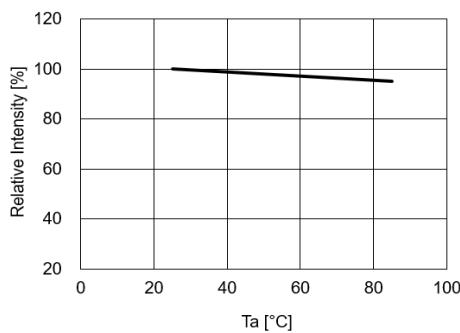


Fig.4 – Forward Voltage (@20mA) vs. Ambient Temperature

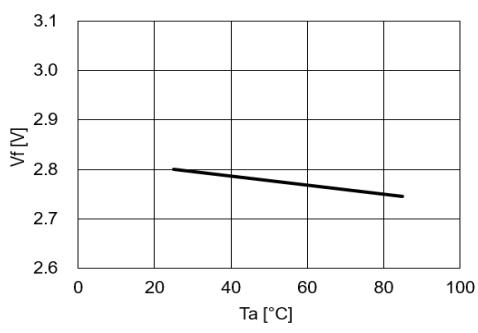


Fig.5 – Dominant Wavelength (@20mA) vs. Ambient Temperature

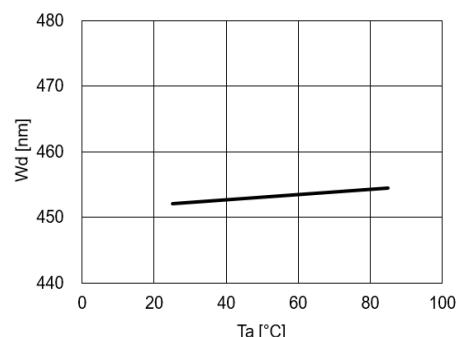


Fig.6 – Maximum Driving Forward DC Current vs. Ambient Temperature (De-rating based on T_j max. = 125°C)

